

Polymeric Tin Carbide Synthetized by Matrix Assisted Pulsed Laser Evaporation.

Jandová, Věra 2016

Dostupný z http://www.nusl.cz/ntk/nusl-260855

Dílo je chráněno podle autorského zákona č. 121/2000 Sb.

Tento dokument byl stažen z Národního úložiště šedé literatury (NUŠL).

Datum stažení: 30.08.2024

Další dokumenty můžete najít prostřednictvím vyhledávacího rozhraní nusl.cz .

Polymeric tin carbide synthetized by matrix assisted pulsed laser evaporation

V. Jandová*, R. Fajgar, V. Dřínek
Institute of Chemical Process Fundamentals ASCR, Rozvojová 135, 165 02 Prague 6, CZ
*The corresponding author e-mail: jandova@icpf.cas.cz

Keywords: MAPLE, tin, XPS, carbide

Technological progress in electronics, photovoltaics, automotive industry etc. drives a need for novel materials. Various polymers, synthetic metals, aerogels, graphene, MAX phases etc. witness this trend worldwide.

Carbides are a large group of compounds between carbon and various elements. In IV group of Mendeleev's table (C, Si, Ge, Sn, Pb) only a single carbide has been known – silicon carbide. In case of other elements, it is believed that crystalline carbide do not exist due to a large difference between carbon and tin (germanium) atomic radii. However, amorphous germanium carbide has been prepared yet. Moreover, some theoretical works indicate that crystalline carbides of Sn and Ge could exist [1].

Polymeric SnCx films were synthetized by MAPLE technique (Matrix Assisted Pulsed Laser Evaporation). Organotin precursors tetravinyltin Sn(CH=CH₂)₄ and/or hexamethylditin Sn₂(CH₃)₆ with a solvent were frozen and subsequently as a target irradiated by TEA CO₂ laser and evaporated. Double bonds caused polymerization due to both irradiation and heating of substrates (up to 250 °C). As the films are extremely sensitive towards ambient (oxygen, water), they were immediately analyzed by XP spectroscopy after synthesis. Raman and UV-Vis spectroscopies have shown that carbon is not graphitized and only sp³ form is present.

Reference

TIL

211

511

Di i

Pil

[1] X. Zhang, S. Quan, C. Ying, Z. Li, Solid State Communications, 151, 1545-1549 (2011)

Acknowledgments

This work was supported by the Grant Agency of the Czech Republic (grant No. 15-08842J).